# **BLP25M710**

# **Broadband LDMOS driver transistor**

Rev. 1 — 29 August 2013

**Product data sheet** 

### 1. Product profile

### 1.1 General description

A 10 W LDMOS power transistor for broadcast and industrial applications in the HF to 2500 MHz band.

Table 1. Application information

Test signal	f (MHz)	I <sub>Dq</sub> (mA)	V <sub>DS</sub> (V)	P <sub>L</sub> (W)	G <sub>p</sub> (dB)	η <sub>D</sub> (%)	IMD <sub>shldr</sub> (dBc)	PAR (dB)
DVB-T	858	110	28	1	20.9	17.1	-47.5 [ <u>1]</u>	9.5 [2]
Pulsed RF 3	2450	80	28	10	16.2	64.5	-	-

<sup>[1]</sup> Measured [dBc] with delta marker at 4.3 MHz from center frequency.

### 1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 2500 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications



<sup>[2]</sup> PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

<sup>[3]</sup> Measured at  $\delta$  = 10 %,  $t_p$  = 12  $\mu$ s.

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## 2. Pinning information

Table 2. Pinning

	9		
Pin	Description	Simplified outline	Graphic symbol
1, 6, 7, 12	n.c.	40 7	40.44
2, 3	gate1	12 7	10, 11 .
4, 5	gate2		<b>⊢</b>   <b>⊷</b> 1
8, 9	drain2		2, 3 — 13
10, 11	drain1	<u> </u>	4, 5
13	source	[1] Transparent top view	'i¬
			8, 9
			aaa-008925

<sup>[1]</sup> Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BLP25M710	HVSON12	plastic thermal enhanced very thin small outline package; no leads; 12 terminals; body $6\times4\times0.85$ mm	SOT1179-2			

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

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## 5. Recommended operating conditions

See application note AN11198 for more details.

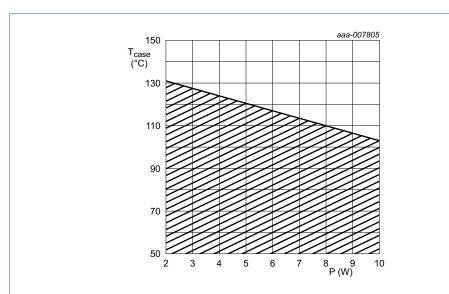


Fig 1. Recommended operating area; case temperature as a function of power dissipation

### 6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 70  ^{\circ}C;  P_{L} = 2  W$	3.2	K/W

### 7. Characteristics

Table 6. DC characteristics

 $T_j = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.18 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 18 \text{ mA}$	1.5	1.9	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-1.4	-	+1.4	μА
$I_{DSX}$	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V}$	-	3.2	-	Α
$I_{GSS}$	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 18 \text{ mA}$	-	160	-	mS
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}; I_D = 630 \text{ mA}$	-	1000	-	mΩ

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Table 7. RF characteristics

Test signal: 1-tone pulsed;  $t_p$  = 50  $\mu$ s;  $\delta$  = 10 %; f = 2140 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 110 mA;  $T_{case}$  = 25 °C; unless otherwise specified, in a production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$G_p$	power gain	$P_{L(AV)} = 2 W$	15	16	-	dB
$\eta_{D}$	drain efficiency	$P_{L(AV)} = 2 W$	20	23	-	%
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		11	-	-	W
RLin	input return loss	$P_{L(AV)} = 2 W$	-	-16	-12	dB

### 8. Test information

### 8.1 Ruggedness in class-AB operation

The BLP25M710 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dq}$  = 110 mA;  $P_{L}$  = 10 W (CW).

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## 9. Package outline

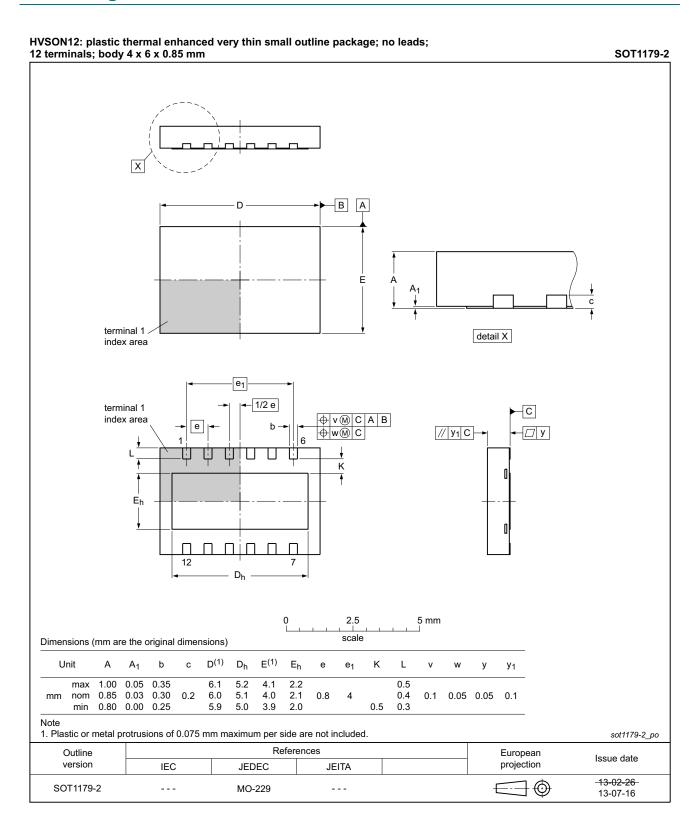


Fig 2. Package outline SOT1179-2 (HVSON12)

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## 10. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

## 11. Abbreviations

Table 8. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DVB-T	Digital Video Broadcast - Terrestrial
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
PAR	Peak-to-Average Ratio
VSWR	Voltage Standing-Wave Ratio

## 12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP25M710 v.1	20130829	Product data sheet	-	-

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## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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